


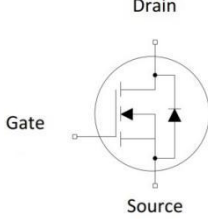



N-channel 650V, 4A, 1.0Ω Super-Junction Power MOSFET

<p>Description</p> <p>Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFET , designed according to the SJ principle. The resulting device has extremely low on resistance,making it especially suitable for applications which require superior power density and outstanding efficiency.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Very low FOM $R_{DS(on)} \times Q_g$ ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction (PFC). ◆ Switched mode power supplies (SMPS). ◆ Uninterrupted power supply (UPS). 	<p>Product Summary</p> <table> <tr> <td>$V_{DS} @ T_{j,25^\circ C}$</td> <td>650V</td> </tr> <tr> <td>$R_{DS(on),max}$</td> <td>1.0Ω</td> </tr> <tr> <td>I_D</td> <td>4.0A</td> </tr> <tr> <td>$Q_{g,typ}$</td> <td>9.1 nC</td> </tr> </table> <div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  <p>TO-252</p> </div> <div style="text-align: center;">  <p>TO-251</p> </div> <div style="text-align: center;">  <p>TO-220F</p> </div> </div> <div style="text-align: center; margin-top: 20px;">  <p>N-Channel MOSFET</p> </div> <div style="text-align: center; margin-top: 20px;">  </div>	$V_{DS} @ T_{j,25^\circ C}$	650V	$R_{DS(on),max}$	1.0Ω	I_D	4.0A	$Q_{g,typ}$	9.1 nC
$V_{DS} @ T_{j,25^\circ C}$	650V								
$R_{DS(on),max}$	1.0Ω								
I_D	4.0A								
$Q_{g,typ}$	9.1 nC								

Marking information

Product	Package	Marking	Packing method
RMA65R1K0SN	TO-252	RMA65R1K0SN	Reel
RMG65R1K0SN	TO-251	RMG65R1K0SN	Tube
RMC65R1K0SN	TO-220F	RMC65R1K0SN	Tube

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^\circ C$)	I_D	4	A
($T_C = 100^\circ C$)		2.5	A
Pulsed drain current ¹⁾	I_{DM}	12	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	50	mJ
Avalanche current, repetitive ³⁾	I_{AR}	0.9	A
Power Dissipation TO-252 /TO-251 ($T_C = 25^\circ C$)	P_D	37	W
- Derate above 25°C		0.3	W/°C
Power Dissipation TO-220F ($T_C = 25^\circ C$)	P_D	30	W
- Derate above 25°C		0.24	W/°C
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	4	A

Diode pulse current	$I_{S,pulse}$	12	A
---------------------	---------------	----	---

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO252/TO-251	TO-220F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.8	4.4	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	73	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wave soldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	260	$^{\circ}\text{C}$

Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=250\mu\text{A}$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.5		4.0	V
Drain cut-off current	I_{DSS}	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^{\circ}\text{C}$ $T_j = 125^{\circ}\text{C}$	- -	- 10	1	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=30\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-30\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=2\text{ A}$ $T_j = 25^{\circ}\text{C}$	- - -	0.88	1.0	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	-	315	-	pF
Output capacitance	C_{oss}		-	27	-	
Reverse transfer capacitance	C_{rss}		-	1.2	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 2\text{ A}$ $R_G = 25\Omega, V_{GS}=10\text{ V}$	-	9.4	-	ns
Rise time	t_r		-	22.6	-	
Turn-off delay time	$t_{d(off)}$		-	36.4	-	
Fall time	t_f		-	25.4	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=520\text{ V}, I_D=2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	2.1	-	nC
Gate to drain charge	Q_{gd}		-	4.0	-	
Gate charge total	Q_g		-	9.1	-	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=2\text{ A}$	-	0.85	-	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F=2\text{ A},$ $dI_F/dt=100\text{ A}/\mu\text{s}$	-	159	-	ns
Reverse recovery charge	Q_{rr}		-	0.93	-	μC
Peak reverse recovery current	I_{rrm}		-	11.2	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.
2. $I_{AS} = 1A$, $V_{DD} = 50V$, Starting $T_j = 25^{\circ}C$.

Electrical Characteristics Diagrams

Figure 1. Output Characteristics

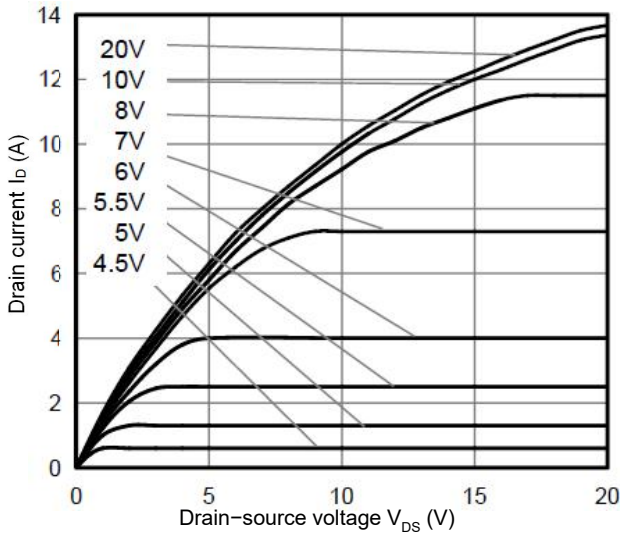


Figure 2. Transfer Characteristics

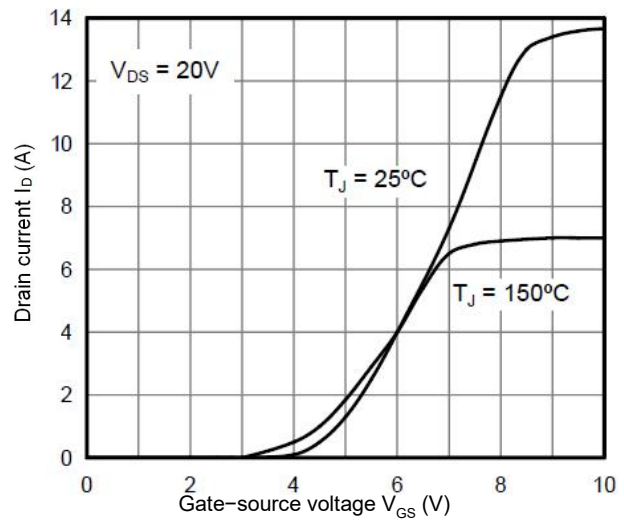


Figure 3. On-Resistance vs. Drain Current

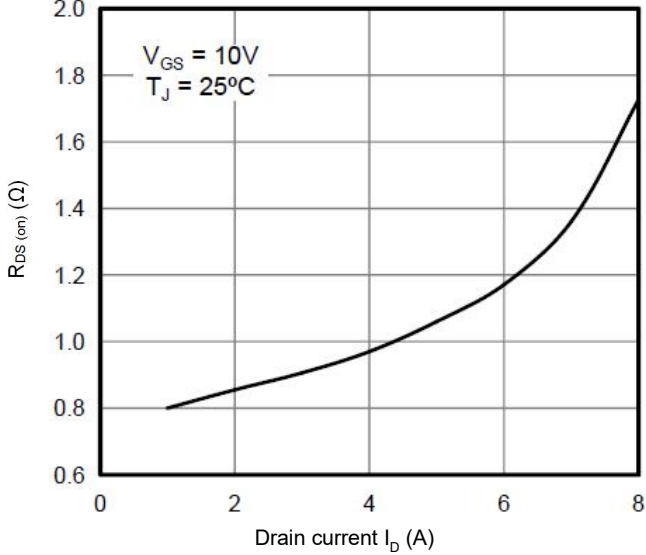


Figure 4. Capacitance Characteristics

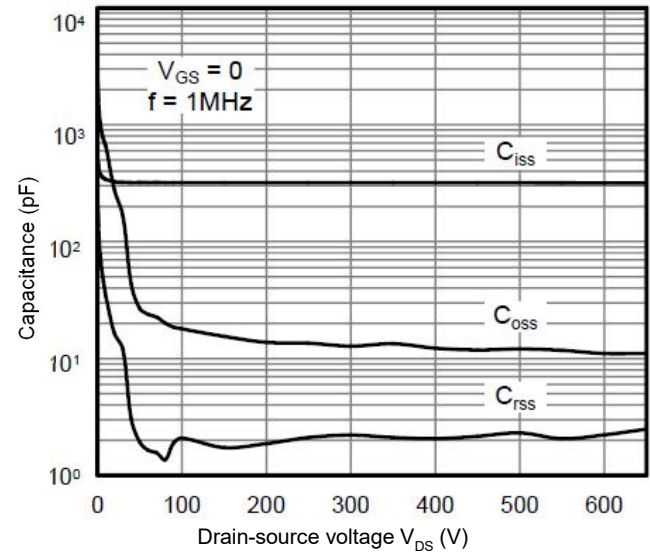


Figure 5. Gate Charge Characteristics

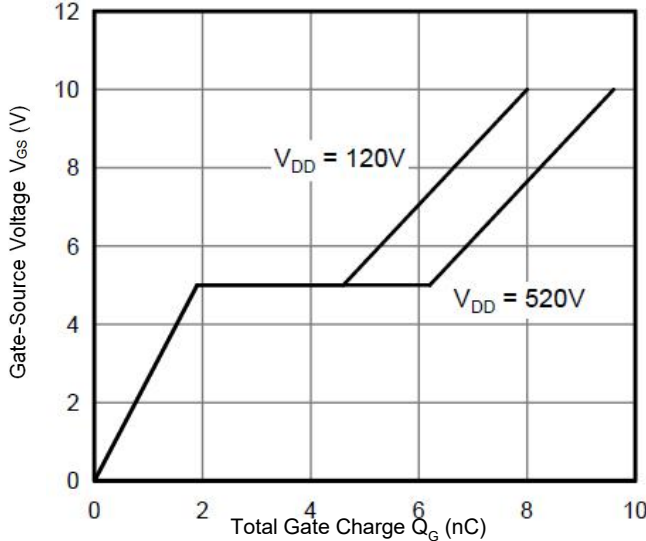


Figure 6. Body Diode Forward Voltage

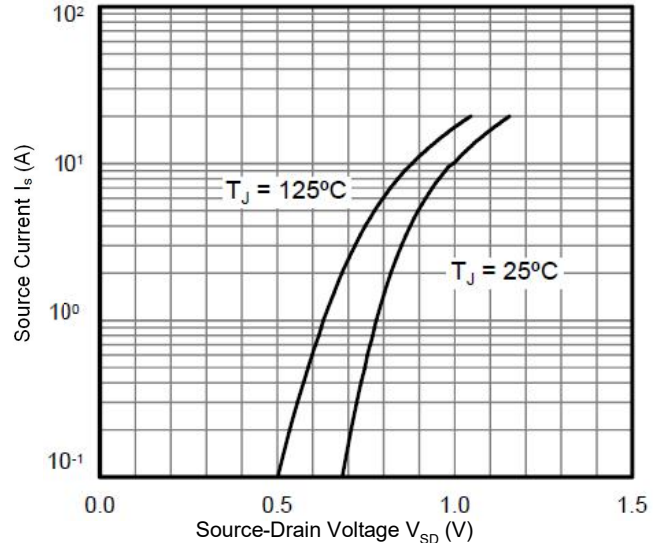


Figure 7. Breakdown Voltage vs. Temperature

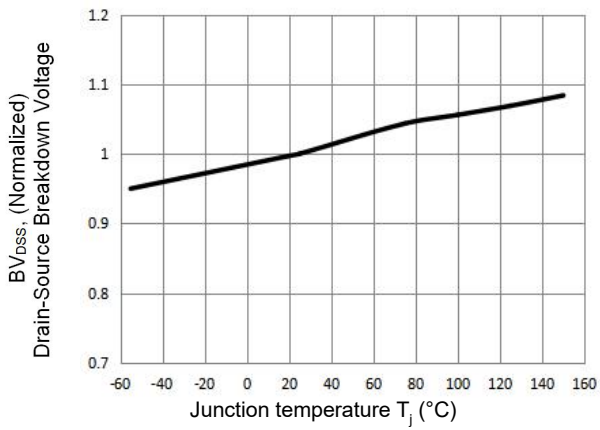


Figure 8. On-Resistance vs. Temperature

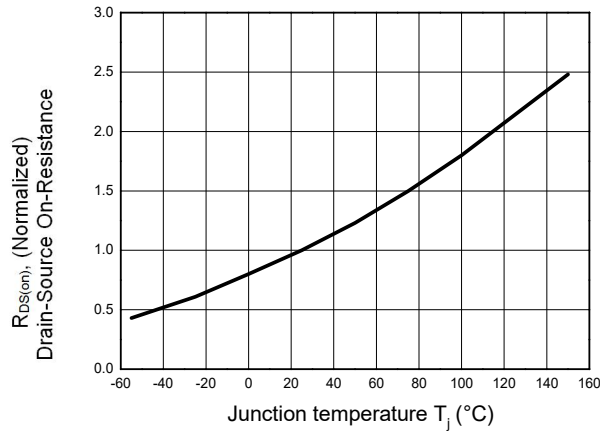


Figure 9. Maximum Safe Operating Area
TO-252/TO-251

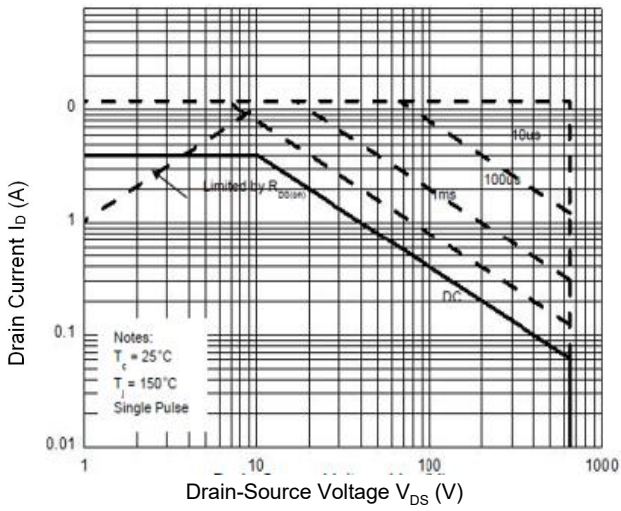
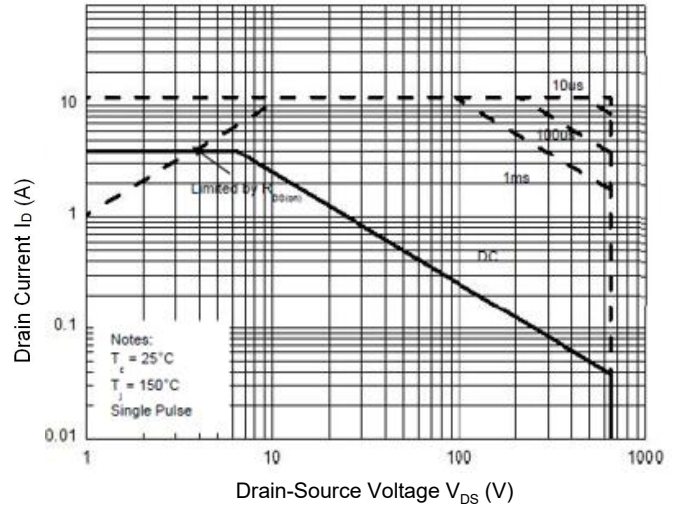
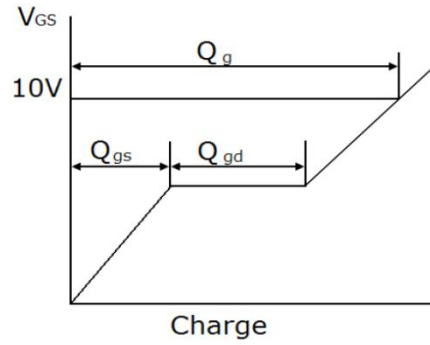
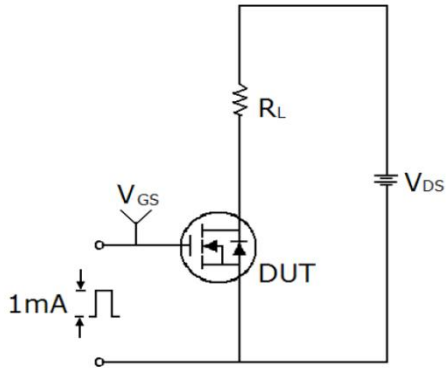


Figure 10. Maximum Safe Operating Area
TO-220F

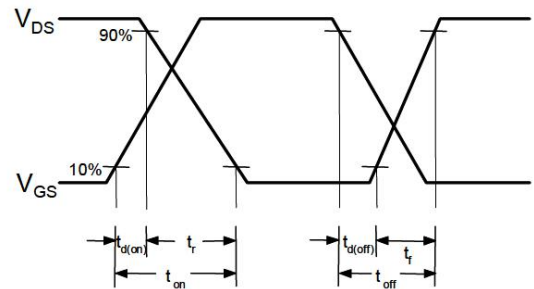
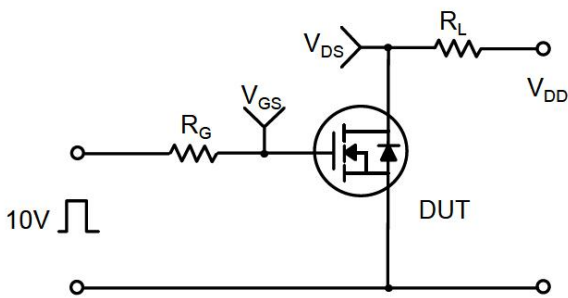


Test Circuits

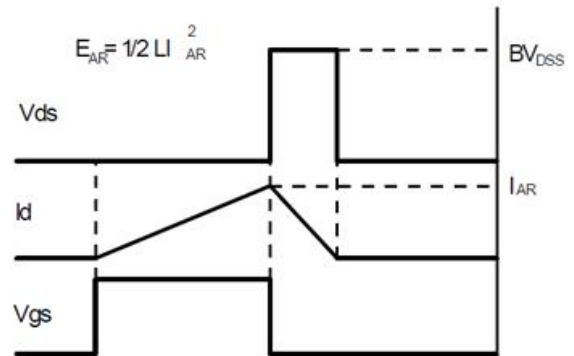
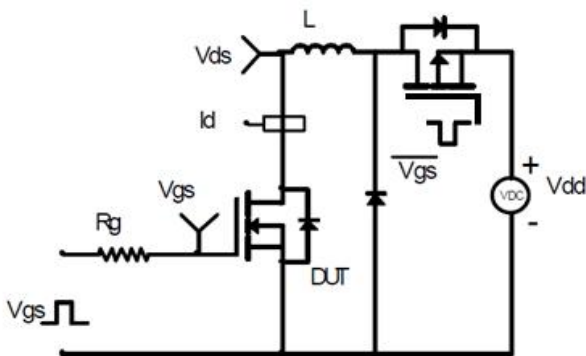
Gate Charge Test Circuit & Waveform



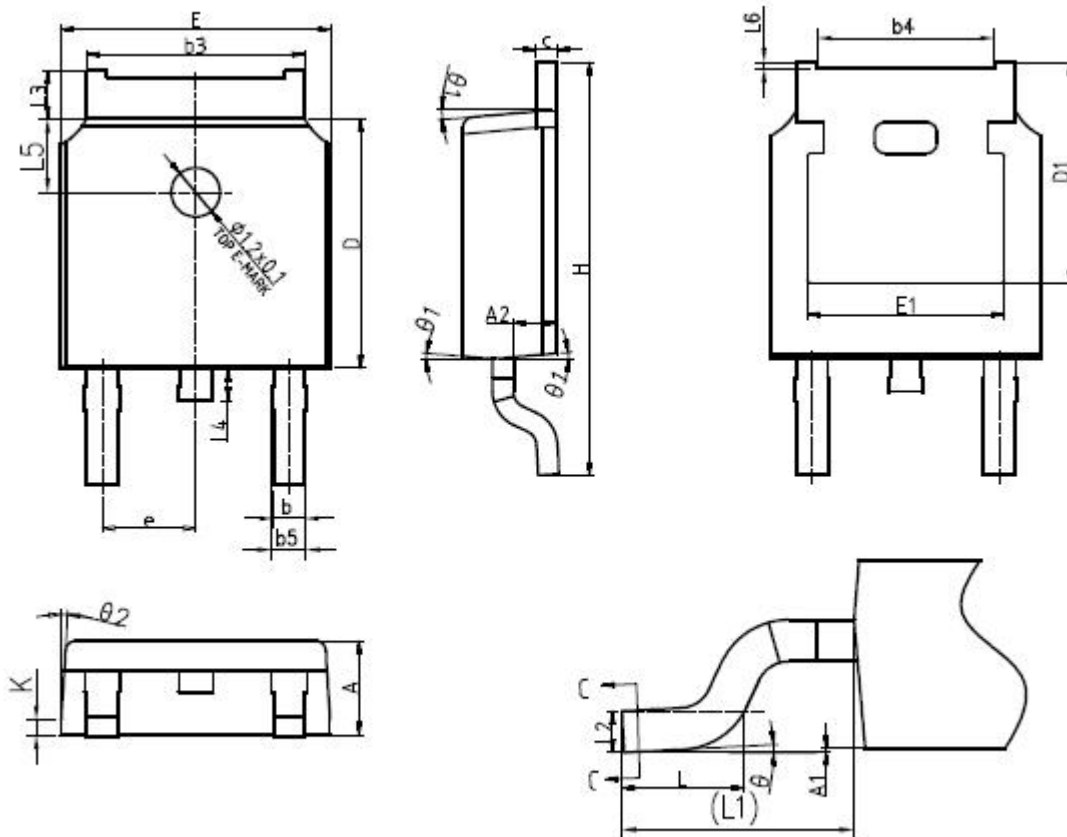
Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Mechanical Dimensions for TO-252

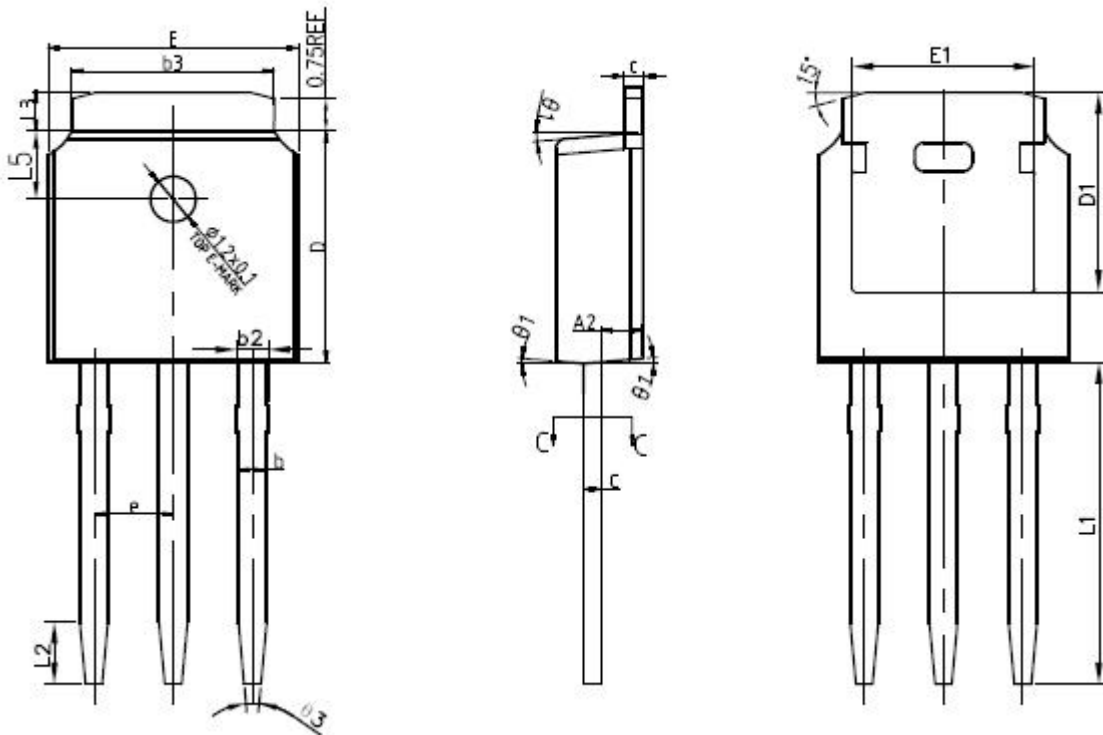


单位: mm

SYMBOL	mm		
	MIN	NOM	MAX
*A	2.20	2.30	2.38
*A1	0.00	-	0.10
A2	0.97	1.07	1.17
*b	0.72	0.78	0.85
b1	0.71	0.76	0.81
*b3	5.23	5.33	5.46
b4	4.27	4.32	4.37
b5	0.72	0.88	0.93
*c	0.47	0.53	0.58
c1	0.46	0.51	0.56
*D	6.00	6.10	6.20
D1	5.30REF		

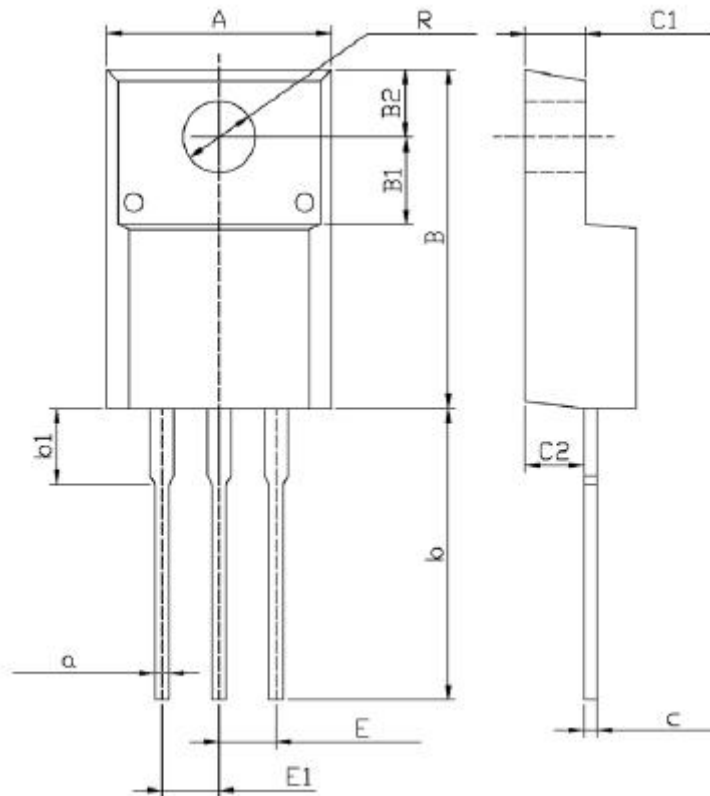
*E	6.50	6.60	6.70
E1	4.70	4.83	4.92
*e	2.286BSC		
L	1.40	1.50	1.70
L1	2.90REF		
L2	0.51BSC		
*L3	0.90	-	1.25
*L4	0.60	0.80	1.00
L5	1.70	1.80	1.90
L6	0	0.047	0.123
θ	0°	-	8°
*θ1	5°	7°	9°
θ2	5°	7°	9°
K	0.40REF		

Mechanical Dimensions for TO-251



SYMBOL	MM		
	MIN	NOM	MAX
*A	2.20	2.30	2.38
*A2	0.97	1.07	1.17
*b	0.72	0.78	0.85
b1	0.71	0.76	0.81
*b2	0.72	0.88	0.95
*b3	5.23	5.33	5.46
*c	0.47	0.53	0.58
c1	0.46	0.51	0.56
*D	6.00	6.10	6.20
D1	5.30REF		
*E	6.50	6.60	6.70
E1	4.70	4.83	4.92
*e	2.286BSC		
*L1	9.20	9.40	9.60
L2	1.25	1.35	1.45
*L3	0.90	1.02	1.25
L5	1.70	1.80	1.90
* $\theta 1$	5°	7°	9°
$\theta 2$	5°	7°	9°
$\theta 3$	11°	13°	15°
K	0.40REF		

Mechanical Dimensions for TO-220F



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
B1	3.8	4.0	E1	2.29	2.79
B2	2.9	3.1	C1	2.5	2.9
R	3.0	3.4	C2	2.5	2.7
b	12.5	13.5	c	0.5	0.7

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Reactor-Micro](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [FCA20N60_F109](#) [FDZ595PZ](#) [AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#)
[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [PSMN4R2-30MLD](#)
[TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#)
[NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-](#)
[7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#)
[BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#) [IRF40SC240ARMA1](#) [IPS60R1K0PFD7SAKMA1](#)
[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)